MPS918, MPS3563

MPS918 is a Preferred Device

Amplifier Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
	MPS918 PS3563	V _{CEO}	15 12	Vdc
•	MPS918 PS3563	V _{CBO}	30 30	Vdc
	MPS918 PS3563	V _{EBO}	3.0 2.0	Vdc
Collector Current – Continuous		I _C	50	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C		P _D	350 2.8	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C		P _D	0.85 6.8	W mW/°C
Operating and Storage Junction Temperature Range		T _J , T _{stg}	-55 to +150	ô

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	357	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	147	°C/W

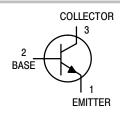
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.



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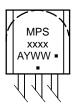
http://onsemi.com



MARKING DIAGRAM



TO-92 CASE 29-11 STYLE 1



MPSxxxx = Device Code

xxxx = 918 or 3563

A = Assembly Location

Y = Year
WW = Work Week
Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MPS918	TO-92	5000 Units/Box
MPS918G	TO-92 (Pb-Free)	5000 Units/Box
MPS3563	TO-92	5000 Units/Box
MPS3563G	TO-92 (Pb-Free)	5000 Units/Box
MPS3563RLRA	TO-92	2000/Tape & Reel
MPS3563RLRAG	TO-92 (Pb-Free)	2000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

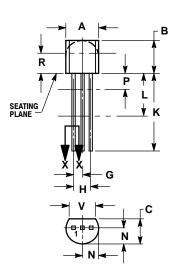
Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS	1		1	-I	
Collector – Emitter Breakdown Voltage (Note 2) $(I_C = 3.0 \text{ mAdc}, I_B = 0)$	MPS918 MPS3563	V _{(BR)CEO}	15 12	_ _	Vdc
Collector – Base Breakdown Voltage ($I_C = 1.0 \mu Adc, I_E = 0$) ($I_C = 100 \mu Adc, I_E = 0$)	MPS918 MPS3563	V _{(BR)CBO}	30 30	- -	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	MPS918 MPS3563	V _{(BR)EBO}	3.0 2.0	- -	Vdc
Collector Cutoff Current (V _{CB} = 15 Vdc, I _E = 0)	MPS918 MPS3563	I _{CBO}	_ _	10 50	nAdc
ON CHARACTERISTICS			•		
DC Current Gain (Note 2) $ (I_C = 3.0 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}) $ $ (I_C = 8.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}) $	MPS918 MPS3563	h _{FE}	20 20	_ 200	-
Collector – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$)	MPS918	$V_{CE(sat)}$	_	0.4	Vdc
Base – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$)	MPS918	V _{BE(sat)}	-	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
$\begin{aligned} & \text{Current-Gain - Bandwidth Product (Note 2)} \\ & \text{(I}_{\text{C}} = 4.0 \text{ mAdc, V}_{\text{CE}} = 10 \text{ Vdc, f} = 100 \text{ MHz)} \\ & \text{(I}_{\text{C}} = 8.0 \text{ mAdc, V}_{\text{CE}} = 10 \text{ Vdc, f} = 100 \text{ MHz)} \end{aligned}$	MPS918 MPS3563	f _T	600 600	_ 1500	MHz
Output Capacitance $(V_{CB} = 0 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$ $(V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$ $(V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	MPS918 MPS918 MPS3563	C _{obo}	- - -	3.0 1.7 1.7	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	MPS918	C _{ibo}	-	2.0	pF
Small-Signal Current Gain (I _C = 8.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	MPS3563	h _{fe}	20	250	-
Noise Figure (I _C = 1.0 mAdc, V_{CE} = 6.0 Vdc, R_{S} = 400 k Ω , f = 60 MHz)	MPS918	NF	-	6.0	dB
FUNCTIONAL TEST			•	•	
$\label{eq:Common-Emitter Amplifier Power Gain} \begin{split} &(I_C=6.0 \text{ mAdc}, V_{CB}=12 \text{ Vdc}, f=200 \text{ MHz}) \\ &(I_C=8.0 \text{ mAdc}, V_{CE}=10 \text{ Vdc}, f=200 \text{ MHz}) \\ &(G_{fd}+G_{re}<-20 \text{ dB}) \end{split}$	MPS918 MPS3563	G _{pe}	15 14	- -	dB
Power Output ($I_C = 8.0 \text{ mAdc}$, $V_{CB} = 15 \text{ Vdc}$, $f = 500 \text{ MHz}$)	MPS918	P _{out}	30	-	mW
Oscillator Collector Efficiency ($I_C = 8.0 \text{ mAdc}, V_{CB} = 15 \text{ Vdc}, P_{out} = 30 \text{ mW}, f = 500 \text{ MHz})$	MPS918	η	25	-	%

^{2.} Pulse Test: Pulse Width $\leq 300 \,\mu s$; Duty Cycle $\leq 1.0\%$.

MPS918, MPS3563

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AL**





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 114-3M, 1902.
 CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R
 IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P AND
- BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
V	0.135		3.43	

STYLE 1:

PIN 1. EMITTER

BASE 2.

COLLECTOR

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